

Docket No.: 4425-317

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

In re Application of

Chun-Pei WU

U.S. Patent Application No. 10/643,964

Filed: August 20, 2003

Group Art Unit: 2823

Examiner: HSIEN MING LEE

For: METHOD FOR FABRICATING A MASK READ-ONLY-MEMORY WITH DIODE CELLS

Dear Sir:

Transmitted herewith is an Amendment in the above identified application.

- ☒ No additional fee is required.  
☐ Small entity status of this application has been established.  
☐ Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	20	20	0	x \$ 18 =	\$ 0.00
Independent Claims	2	3	0	x \$ 86 =	\$ 0.00
If multiple claims newly presented, add \$290.00					
Fee for extension of time					
<b>TOTAL FEE DUE</b>					<b>\$ 0.00</b>

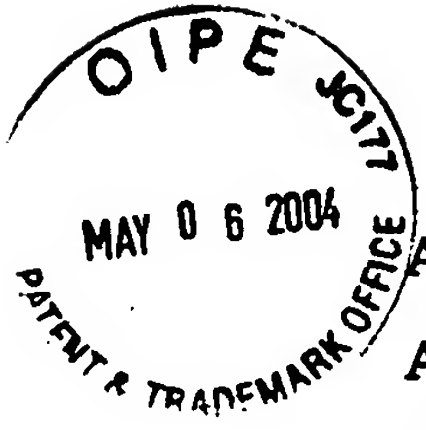
- ☐ A credit card authorization form in the amount of \_\_\_\_\_ is attached
- ☒ The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 07-1337, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**Appl. No.** : 10/643,964  
**Applicant** : Chun-Pei Wu  
**Filed** : August 20, 2003  
**TC/A.U.** : 2823  
**Title** : METHOD FOR FABRICATING A MASK READ-  
ONLY-MEMORY WITH DIODE CELLS  
**Examiner** : LEE, HSIEN MING  
**Docket No.** : 4425-317

Honorable Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**AMENDMENT**

Sir:

In response to the Official Action mailed on February 24, 2004,  
please amend the application as follows :

**Amendments to the Claims** are reflected in the listing of claims which  
begin on page 2 of this paper.

**Remarks/arguments** begin on page 8 of this paper.